P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 40	0.054 at V_{GS} = - 10 V	- 4.5	9
	0.072 at V_{GS} = - 4.5 V	- 3.9	

FEATURES

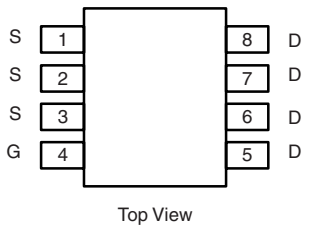
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

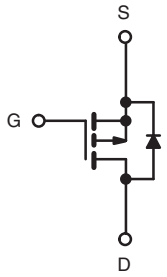
APPLICATIONS

- CCFL Inverter

SO-8



Top View



P-Channel MOSFET

Ordering Information: Si4447DY-T1-E3 (Lead (Pb)-free)
Si4447DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 40		V
Gate-Source Voltage		V_{GS}	± 16		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 4.5	- 3.3	A
	T_A = 70 °C		- 3.6	- 2.7	
Pulsed Drain Current		I_{DM}	- 30		
Continuous Source Current (Diode Conduction)[a]		I_S	- 1.7	- 0.9	
Avalanche Current	L = 0.1 mH	I_{AS}	16		
Single Pulse Avalanche Energy		E_{AS}	13		mJ
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2	1.1	W
	T_A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	50	62.5	°C/W
	Steady State		85	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	30	40	

Notes:
a. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.8		- 2.2	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 40		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			3.4		
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 40 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 40 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 5 V, V_{GS} = - 10 V	- 20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 4.5 A		0.045	0.054	Ω
		V_{GS} = - 15 V, I_D = - 4.5 A		0.059	0.072	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 4.5 A		13		S
Diode Forward Voltage[a]	V_{SD}	I_S = - 1.7 A, V_{GS} = 0 V		- 0.79	- 1.2	V
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 20 V, V_{GS} = 0 V, f = 1 MHz		805		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			85		
Total Gate Charge	Q_g	V_{DS} = - 20 V, V_{GS} = - 4.5 V, I_D = - 4.5 A		9	14	nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			3.6		
Gate Resistance	R_g	f = 1 MHz		11.5	18	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 15 Ω $I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω		8	13	ns
Rise Time	t_r			12	18	
Turn-Off DelayTime	$t_{d(off)}$			74	110	
Fall Time	t_f			38	60	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, dI/dt = 100 A/µs		27	45	
Body Diode Reverse Recovery Charge	Q_{rr}			17	26	nC

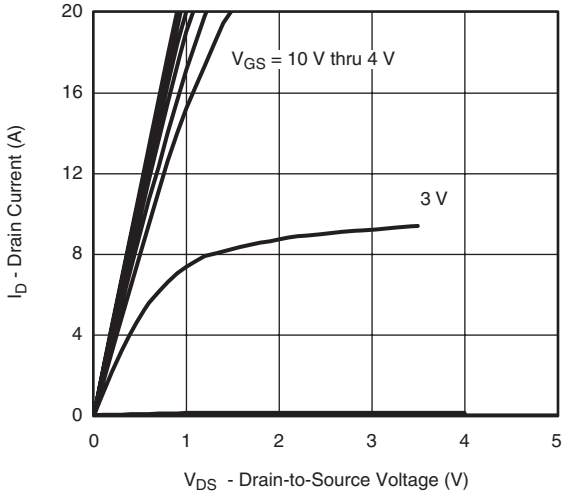
Notes:

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

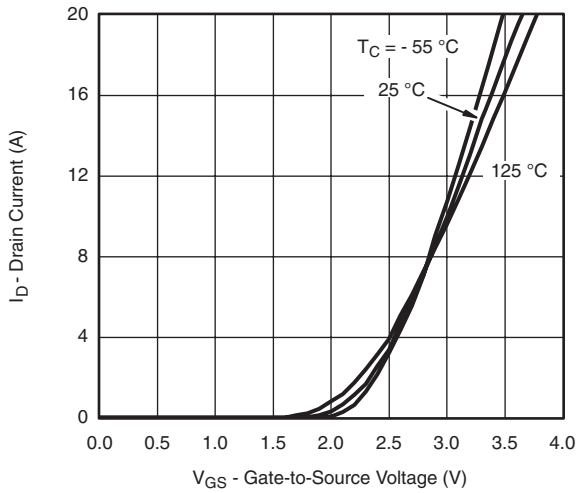
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

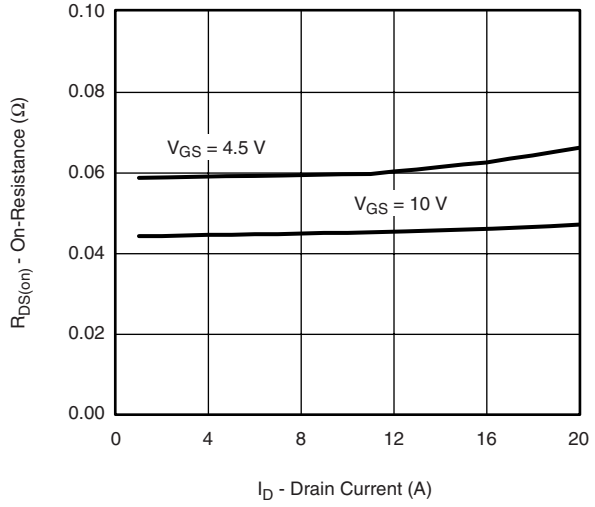


Output Characteristics

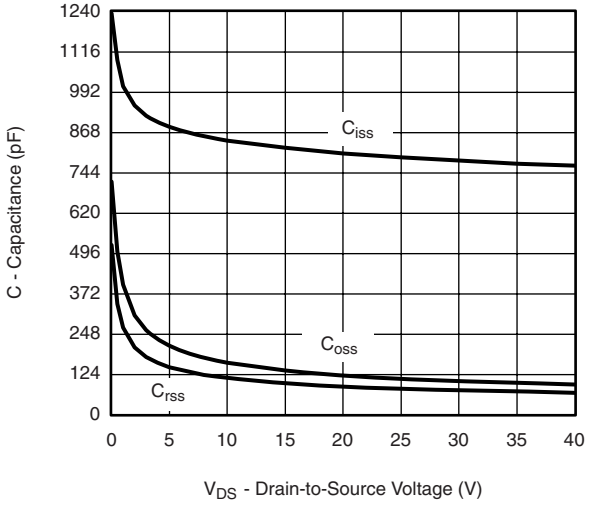


Transfer Characteristics

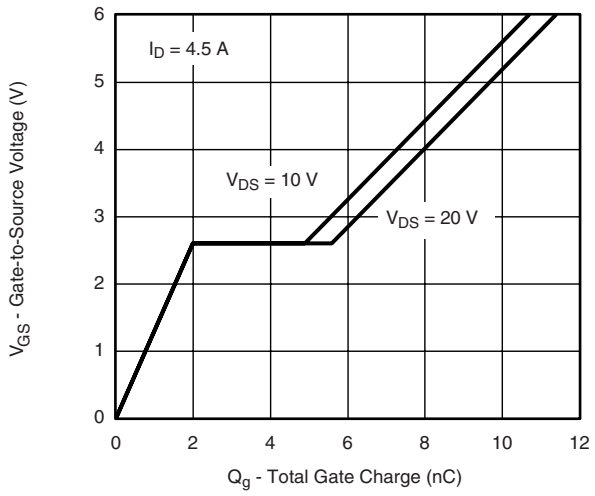
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



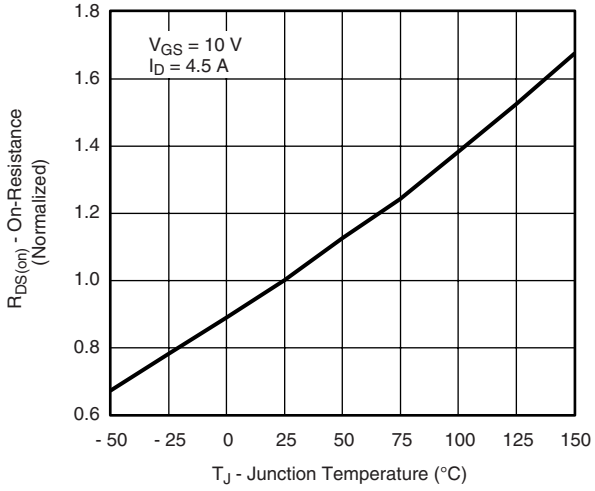
On-Resistance vs. Drain Current



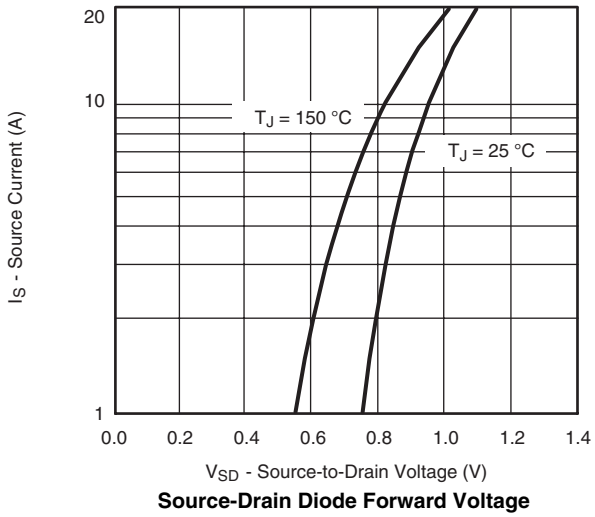
Capacitance



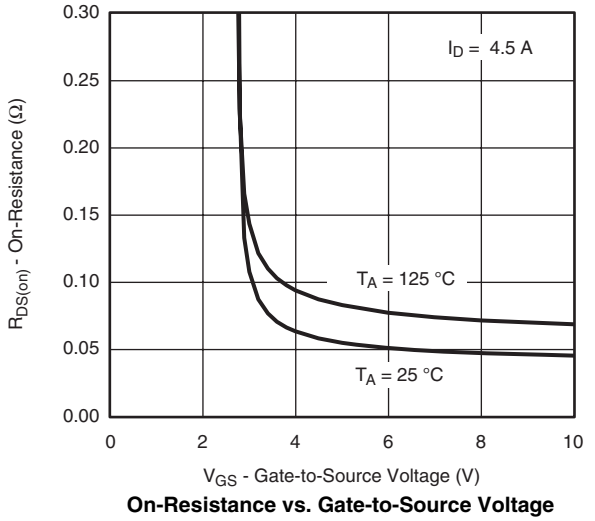
Gate Charge



On-Resistance vs. Junction Temperature

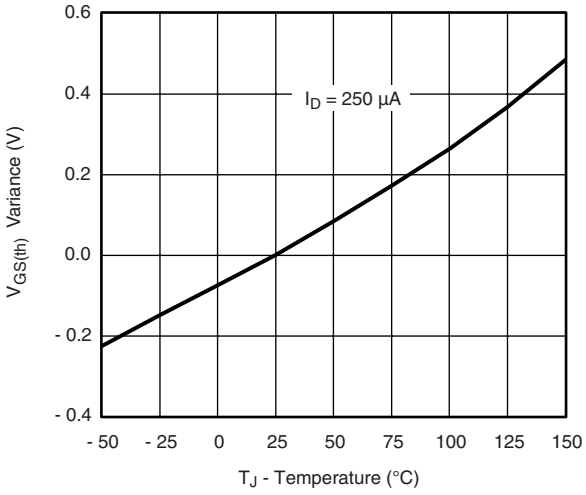


Source-Drain Diode Forward Voltage

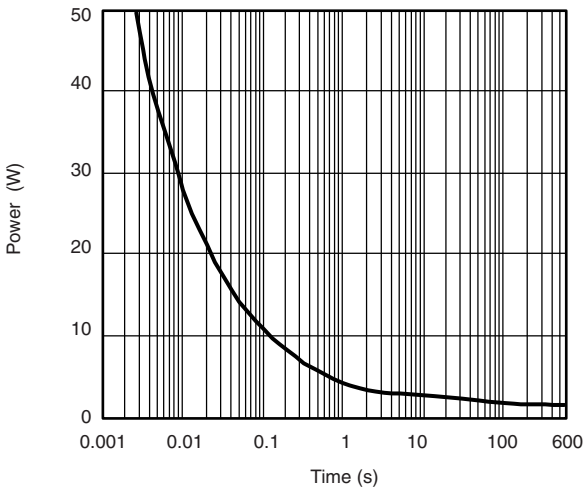


On-Resistance vs. Gate-to-Source Voltage

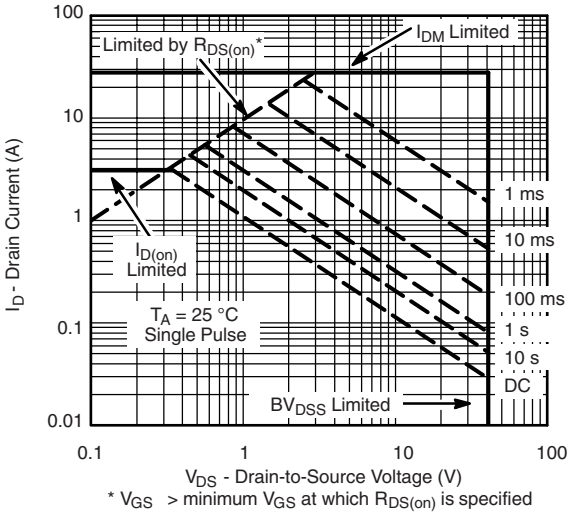
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



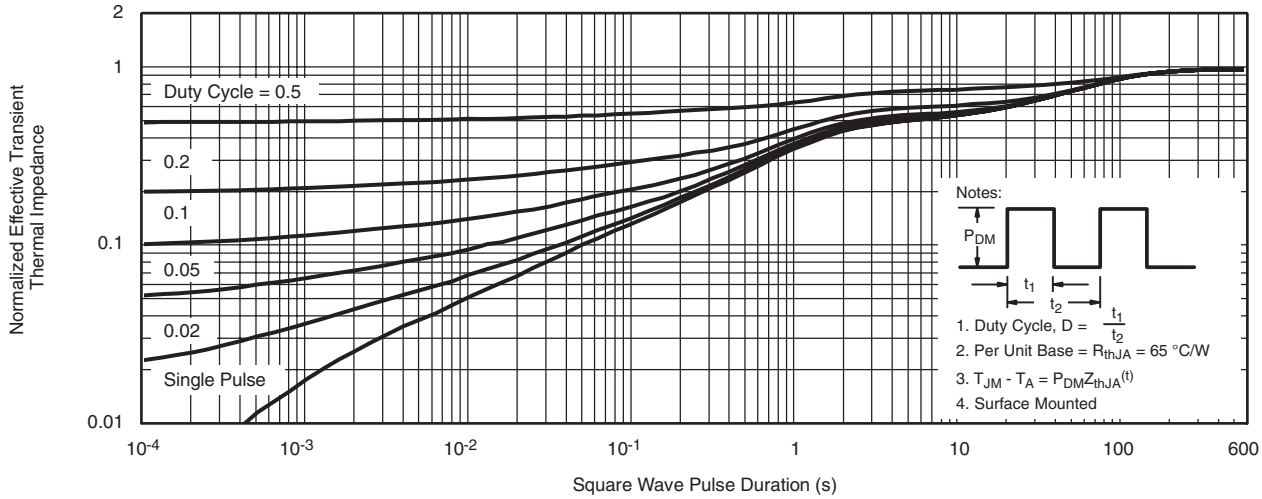
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

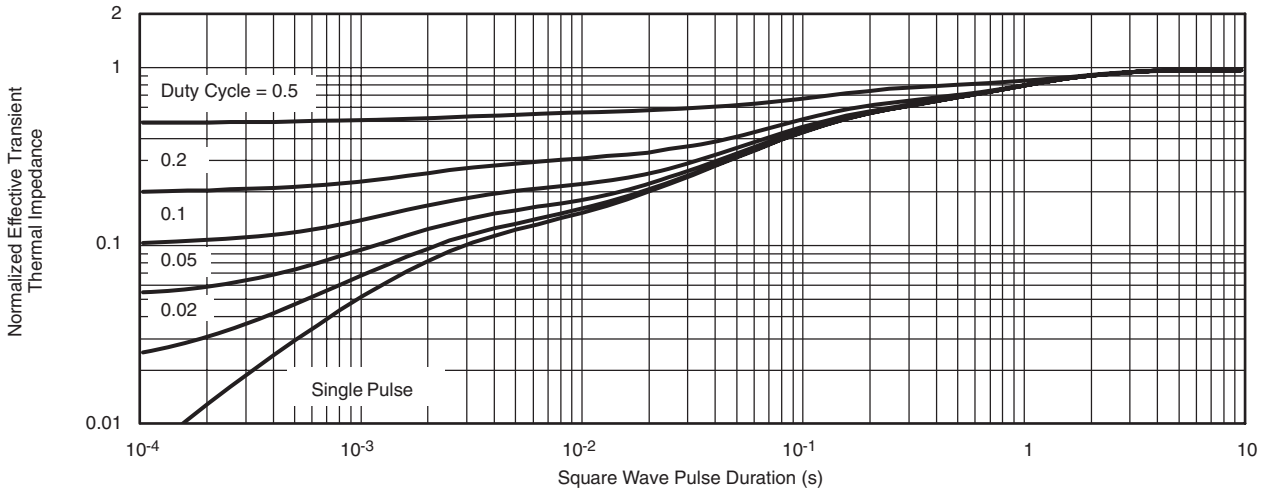


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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